

NTE125 General Purpose Silicon Rectifier

Description:

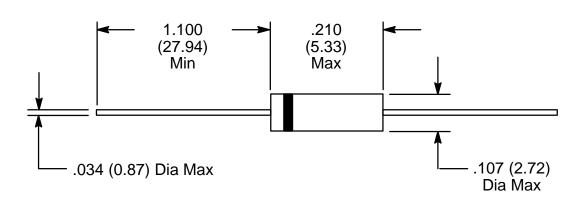
The NTE125 is a general purpose silicon rectifier in a DO41 case designed for low power and switching applications.

Maximum Ratings:

Peak Repetitive Reverse Voltage, V _{RRM}
Working Peak Reverse Voltage, V _{RWM}
DC Blocking Voltage, V _R 1000V
Non-Repetitive Peak Reverse Voltage (Halfwave, Single Phase, 60Hz), V _{RSM}
RMS Reverse Voltage, V _{R(RMS)}
Average Rectified Forward Current. I _O
(Single Phase, Resistive Load, 60Hz, T _A = +75°C)
Non-Repetitive Peak Surge Current, I _{FSM}
(Surge applied at rated load conditions for 1 cycle)
Operating Junction Temperature Range, T _J –65° to +175°C
Storage Temperature Range, T _{stg} –65° to +175°C
Maximum Lead Temperature, T _L
(During Soldering, 3/8" from case for 10sec at 5lbs tension) +350°C

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Maximum Instantaneous Forward Voltage Drop	VF	$i_F = 1A, T_J = +25^{\circ}C$	_	0.93	1.1	V
Maximum Full-Cycle Average Forward Voltage Drop	V _{F(AV)}	I _O = 1A, T _L +75°C, 1" leads	_		8.0	V
Maximum Reverse Current	I _R	$V_{RRM} = 600V, T_J = +25^{\circ}C$	_	0.05	10	μΑ
		$V_{RRM} = 600V, T_{J} = +100^{\circ}C$	_	1.0	50	
Maximum Full-Cycle Average Reverse Current	I _{R(AV)}	I _O = 1A, T _L +75°C, 1" leads	_	-	30	μΑ



Color Band Denotes Cathode